

100V, 116A, 6.0mΩ N-channel Power SGT MOSFET

JMSH1006PC

Features

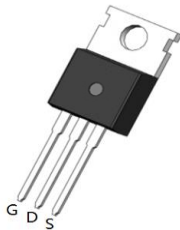
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

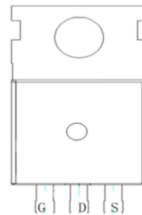
- Load Switch
- PWM Application
- Power Management

Product Summary

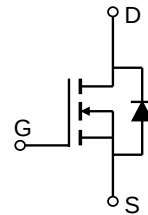
Parameters	Value	Unit
V_{DS}	100	V
$V_{GS(th)}_{Typ}$	3.0	V
$I_D(@V_{GS}=10V)$	116	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	6.0	mΩ



TO-220-3L Top View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Tube(pcs)	Per Carton (pcs)
JMSH1006PC-U	SH1006P	NA	Tube	TO-220-3L	50	5000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	356	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

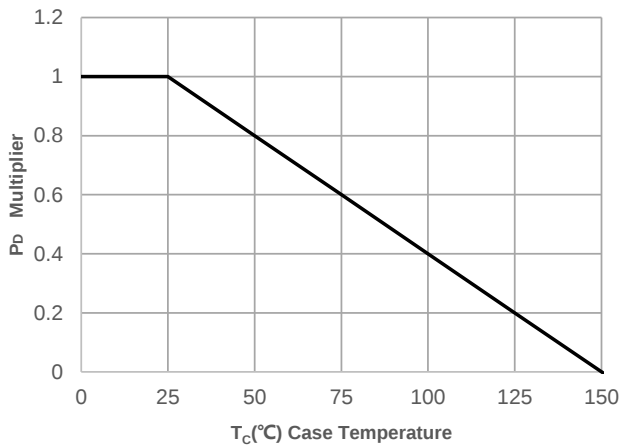
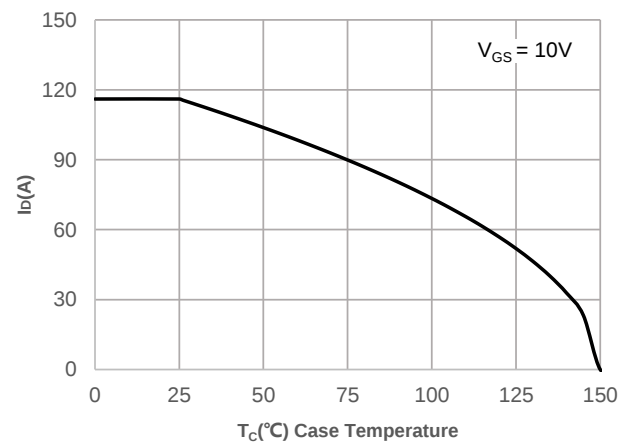
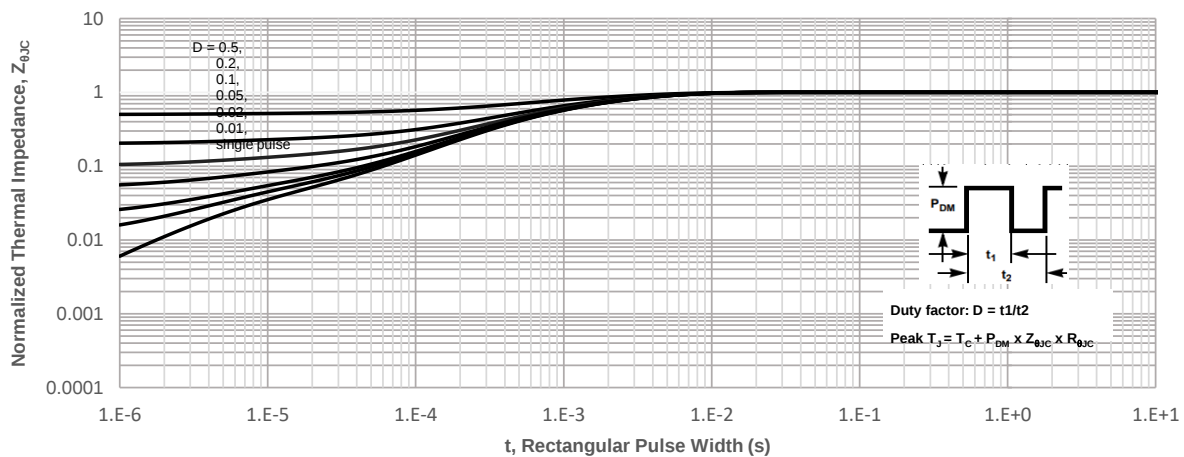
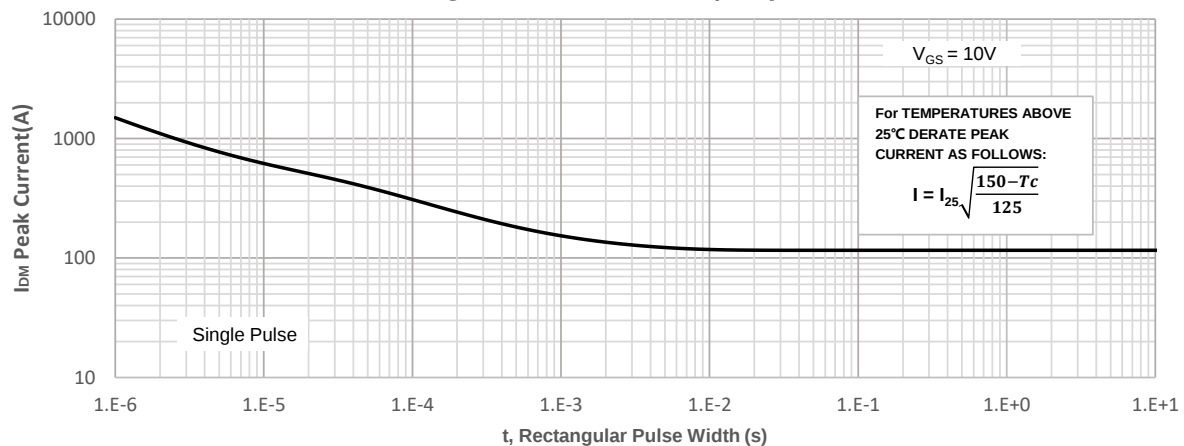
Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	35	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.6	$^\circ\text{C/W}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

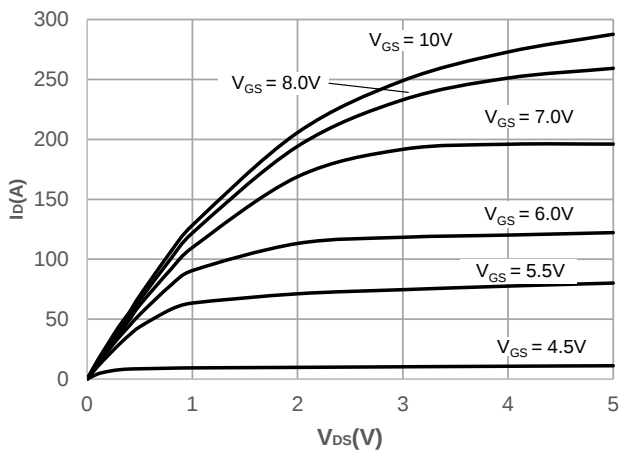
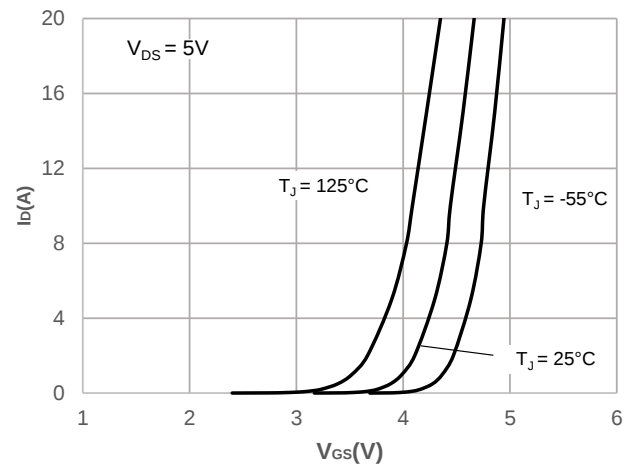
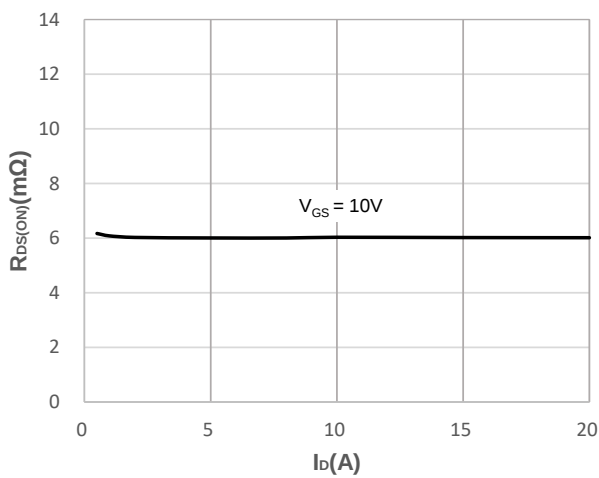
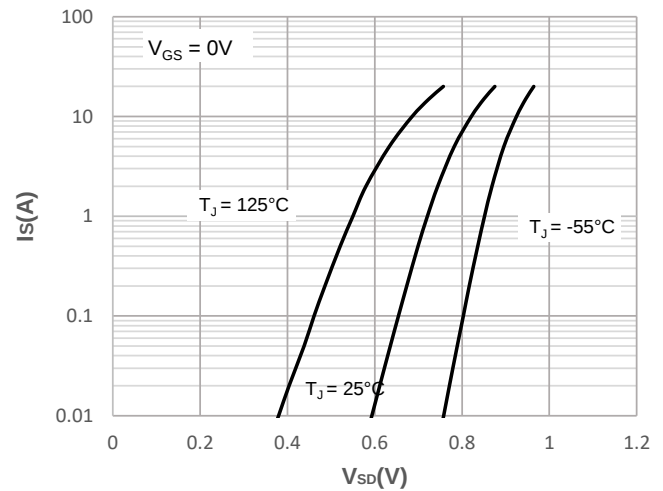
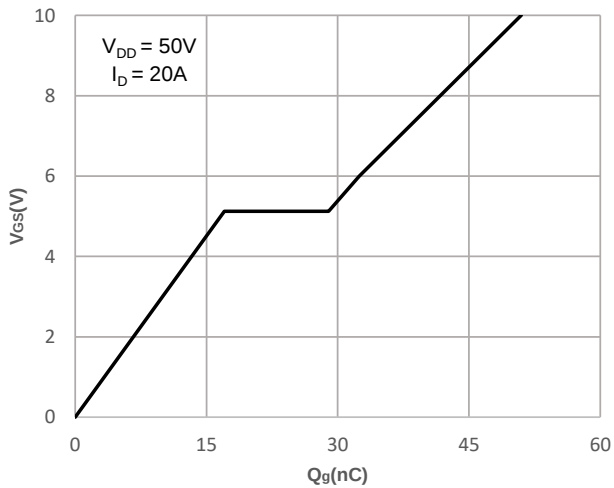
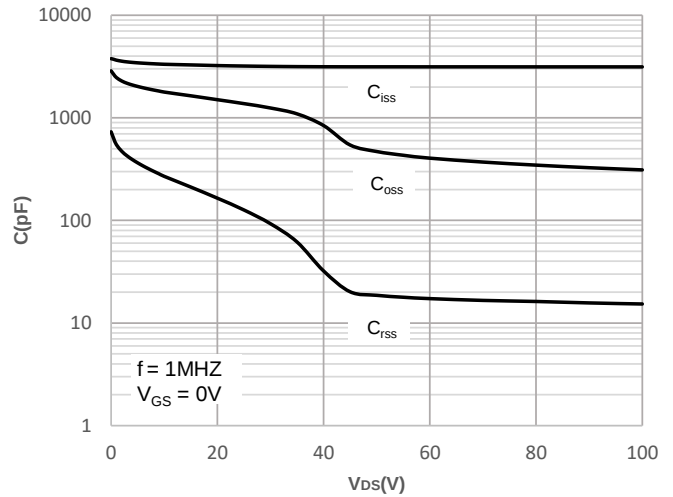
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.1	3.0	3.9	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	6.0	7.8	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	0.6	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	3144	-	pF
C _{oss}	Output Capacitance		-	470	-	pF
C _{rss}	Reverse Transfer Capacitance		-	19	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 20A	-	51	-	nC
Q _{gs}	Gate Source Charge		-	17	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	12	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 20A, R _{GEN} = 2.7Ω	-	15	-	ns
t _r	Turn-On Rise Time		-	18	-	ns
t _{d(off)}	Turn-Off DelayTime		-	27	-	ns
t _f	Turn-Off Fall Time		-	8	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	116	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	464	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 15A, di/dt = 100A/us	-	56	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	106	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 15.4\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

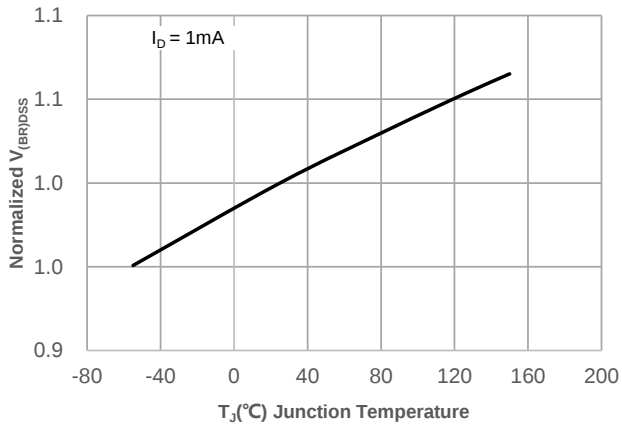


Figure 12: Normalized on Resistance vs. Junction Temperature

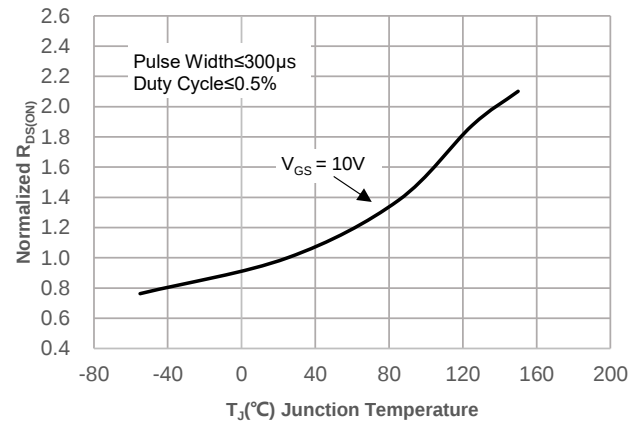


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

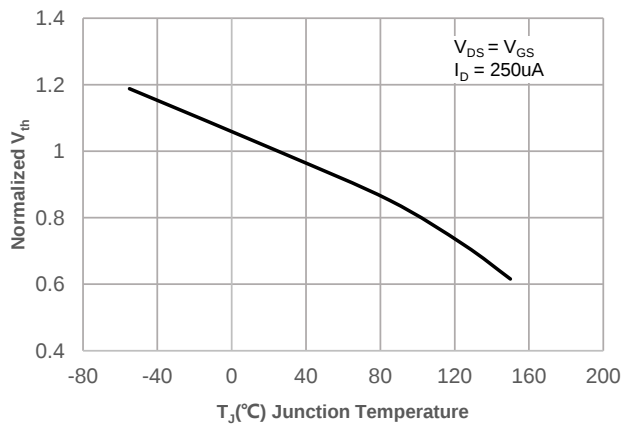


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

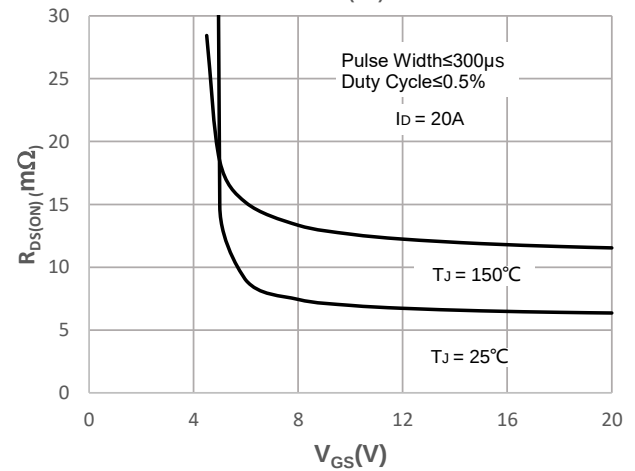
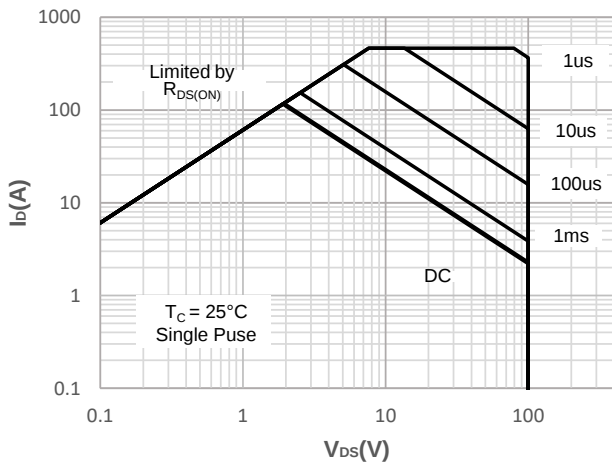


Figure 15: Maximum Safe Operating Area



Test Circuit

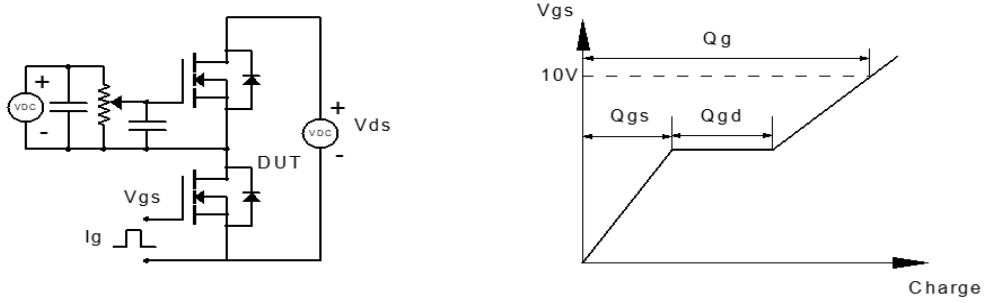


Figure 1: Gate Charge Test Circuit & Waveform

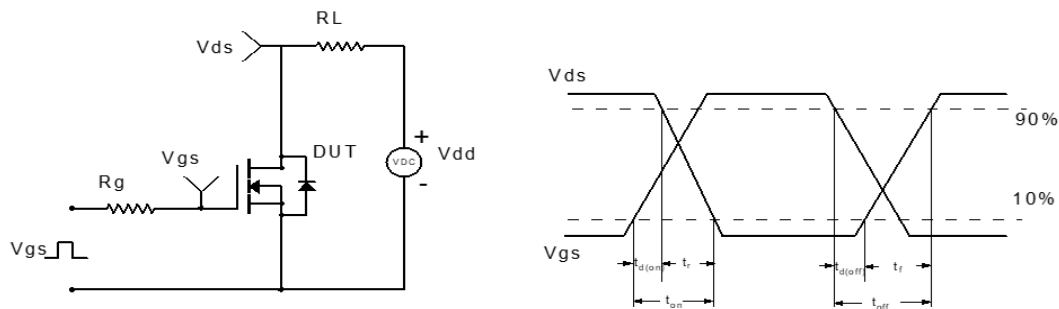


Figure 2: Resistive Switching Test Circuit & Waveform

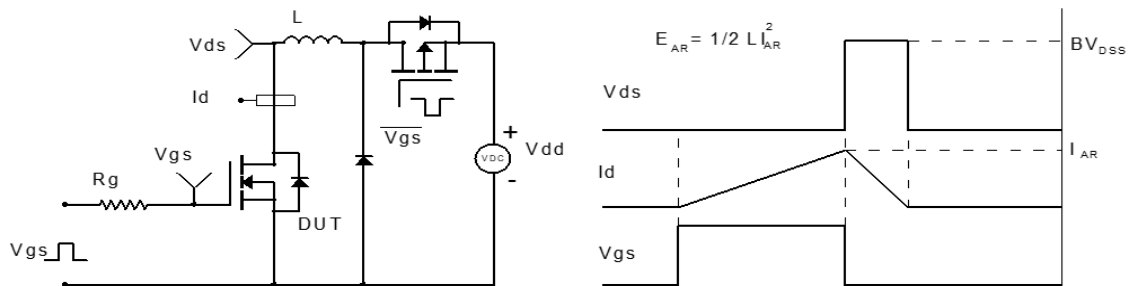


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

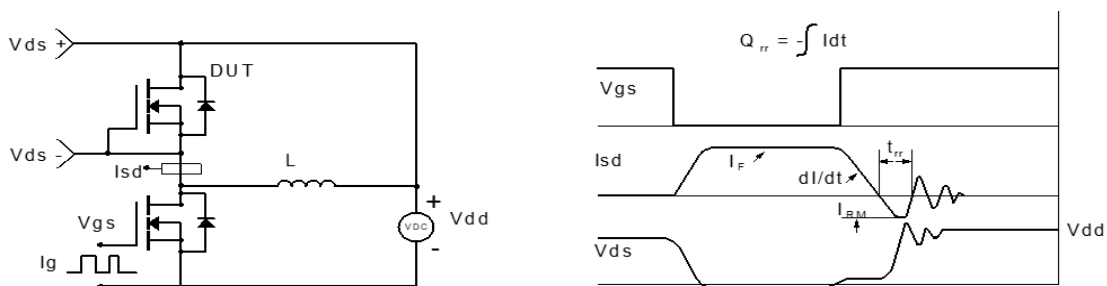
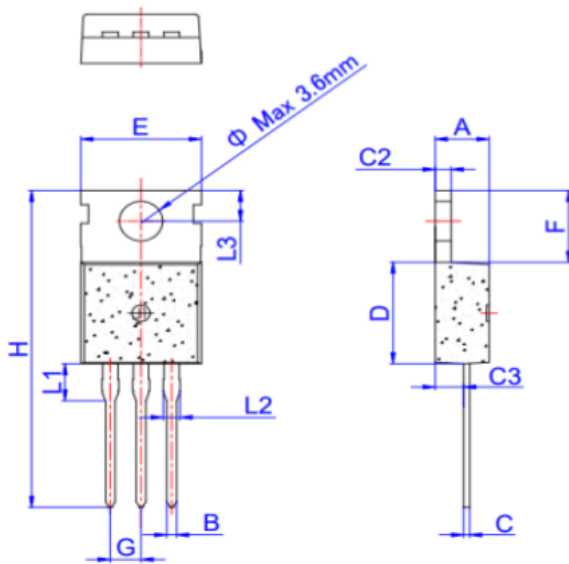


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220C-3L)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

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